

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki, et al.      Art Unit : 1765  
Serial No. : 09/892,225      Examiner : Mathew J. Song  
Filed : June 25, 2001  
Title : SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREFOR

**MAIL STOP AF**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

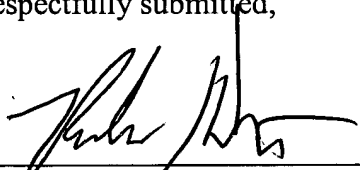
INFORMATION DISCLOSURE STATEMENT

Copies of the references listed on the attached form PTO-1449 are enclosed.

This statement is being filed after a final Office action or a Notice of Allowance, but before payment of the issue fee. A check for \$180 in payment of the late submission fee of §1.17(p) is enclosed. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 11/22/04

  
\_\_\_\_\_  
Roberto J. Devoto  
Reg. No. 55,108

Fish & Richardson P.C.  
1425 K Street, N.W.  
11th Floor  
Washington, DC 20005-3500  
Telephone: (202) 783-5070  
Facsimile: (202) 783-2331

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(Modified)U.S. Department of Commerce  
Patent and Trademark OfficeAttorney's Docket No.  
07977-279001Application No.  
09/892,225**Information Disclosure Statement  
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant  
Shunpei Yamazaki, et al.Filing Date  
June 25, 2001Group Art Unit  
1765**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AJ	JP 04-168769	06/16/1992	Japan			FULL	
	AK							
	AL							
	AM							
	AN							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
	AO	Sasaki et al., "A New Low-Temperature Poly-Si TFT Technology Realizing Mobility above 500 cm <sup>2</sup> /Vs by Using CW Laser Lateral Crystallization (CLC)", Journal of Institute of Electronics, Information and Communication Engineers, C, Vol. J85-C, No. 8, pp. 601-608, August 2002.
	AP	
	AQ	
	AR	

Examiner Signature

Date Considered

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.